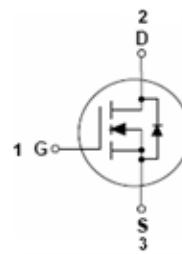


Features

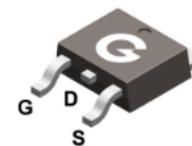
- Low power loss by high speed switching and low on-resistance
- Excellent thermal behavior
- HBM: JESD22-A114-B: 1B
- Product validation acc. JEDEC Standard
- RoHS compliant with Halogen-free

HF



Applications

- PFC power supply stages
- Lighting applications
- Adapter



TO-252

Mechanical Data

- Case: TO-252
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
SJM60R280D	TO-252	80 pcs / Tube & 2500 pcs / Tape & Reel	SJM60R280D

Maximum Ratings (@ $T_c = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	600	V
Gate-to-Source Voltage	V_{GSS}	± 30	V
Continuous Drain Current ($T_c = 25^\circ\text{C}$)	I_D	15	A
Continuous Drain Current ($T_c = 100^\circ\text{C}$)		9.5	A
Pulsed Drain Current ($t_p = 10\mu\text{s}$, $T_c = 25^\circ\text{C}$)	I_{DM}	60	A
Single Pulse Avalanche Energy ³	E_{AS}	300	mJ
Power Dissipation ($T_c = 25^\circ\text{C}$)	P_D	104	W
Operating Junction Temperature Range	T_J	-55 ~ +150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	-	0.9	1.2	$^\circ\text{C}/\text{W}$
Thermal Resistance Junction-to-Air ¹	$R_{\theta JA}$	-	-	62	$^\circ\text{C}/\text{W}$

Electrical Characteristics (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{V}$, $I_D = 250\mu\text{A}$	600	-	-	V
$I_{DS(0)}$	Zero Gate Voltage Drain Current	$V_{DS} = 600\text{V}$, $V_{GS} = 0\text{V}$	-	-	1	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS} = \pm 30\text{V}$, $V_{DS} = 0\text{V}$	-	-	± 100	nA
On Characteristics						
$R_{DS(ON)}$	Drain-Source On-resistance ^{*2}	$V_{GS} = 10\text{V}$, $I_D = 6\text{A}$	-	260	280	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	2.5	3.7	4.5	V
R_G	Gate Resistance	$V_{GS} = 0\text{V}$, $f = 1\text{MHz}$	-	7.6	-	Ω
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$	-	823	-	pF
C_{oss}	Output Capacitance	$V_{DS} = 40\text{V}$	-	67	-	
C_{rss}	Reverse Transfer Capacitance	$f = 250\text{kHz}$	-	0.7	-	
Switching Characteristics						
$t_{d(ON)}$	Turn-on Delay Time ^{*4}	$V_{DD} = 400\text{V}$	-	11	-	ns
t_r	Turn-on Rise Time ^{*4}	$V_{GS} = 10\text{V}$	-	10	-	
$t_{d(OFF)}$	Turn-Off Delay Time ^{*4}	$R_G = 10\Omega$	-	49	-	
t_f	Turn-Off Fall Time ^{*4}	$I_D = 5.3\text{A}$	-	10	-	
Q_G	Total Gate-Charge	$V_{DD} = 520\text{V}$	-	22.5	-	nC
Q_{GS}	Gate to Source Charge	$V_{GS} = 10\text{V}$	-	4.6	-	
Q_{GD}	Gate to Drain (Miller) Charge	$I_D = 8\text{A}$	-	12.8	-	
Source-Drain Diode Characteristics						
V_{SD}	Diode Forward Voltage ^{*2}	$I_{SD} = 6\text{A}$, $V_{GS} = 0\text{V}$	-	-	1.2	V
t_{rr}	Reverse Recovery Time	$I_F = 6\text{A}$, $V_R = 400\text{V}$	-	270	-	ns
Q_{rr}	Reverse Recovery Charge	$di/dt = 100 \text{ A}/\mu\text{s}$	-	2.8	-	μC

Notes:

1. The data tested by surface mounted on a minimum recommended FR-4 board
2. The data tested by pulsed, pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
3. The E_{AS} data shows Max. rating. The test condition is $V_{DD} = 100\text{V}$, $V_{GS} = 15\text{V}$, $L = 50\text{mH}$
4. Guaranteed by design, not subject to production

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

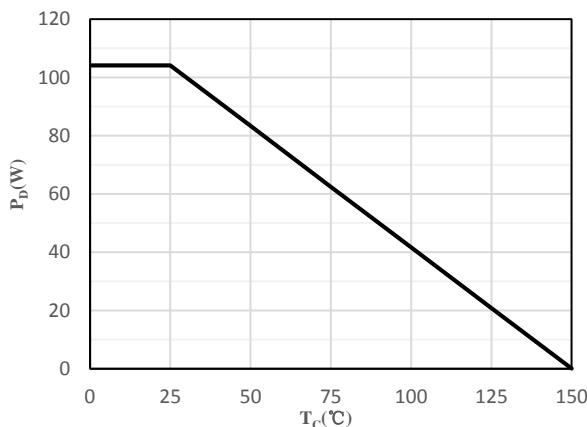


Fig 1 Power Dissipation

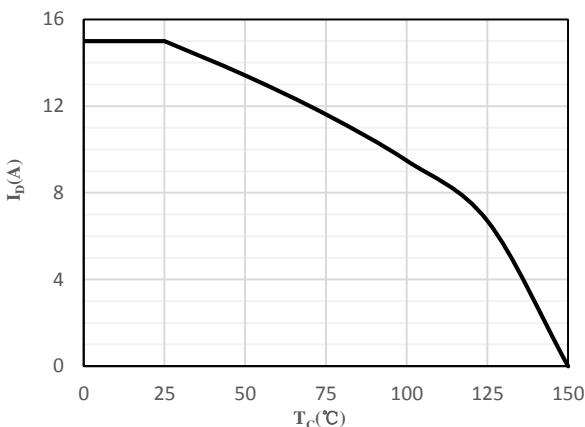


Fig 2 Drain Current

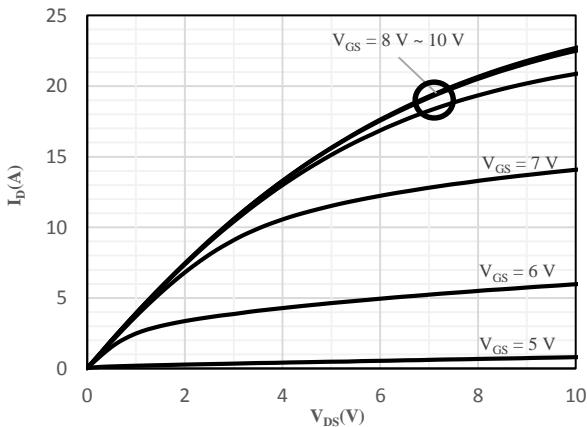


Fig 3 Typical Output Characteristics

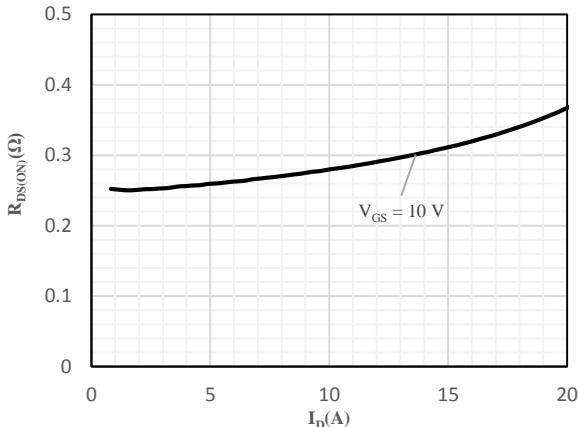


Fig 4 On-Resistance vs. Drain Current

and Gate Voltage

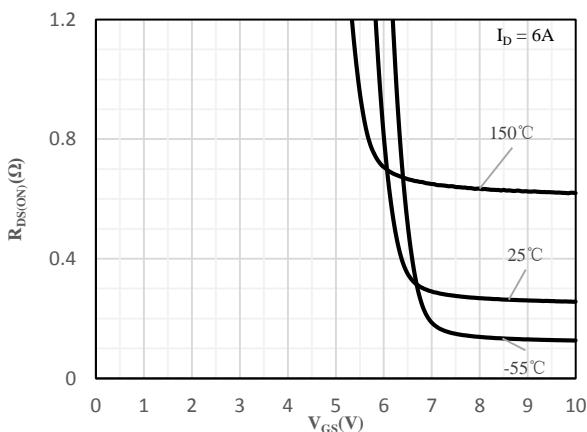


Fig 5 On-Resistance vs. Gate-Source Voltage

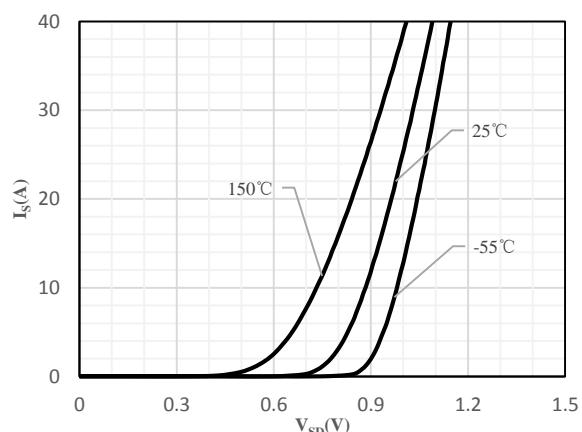


Fig 6 Body-Diode Characteristics

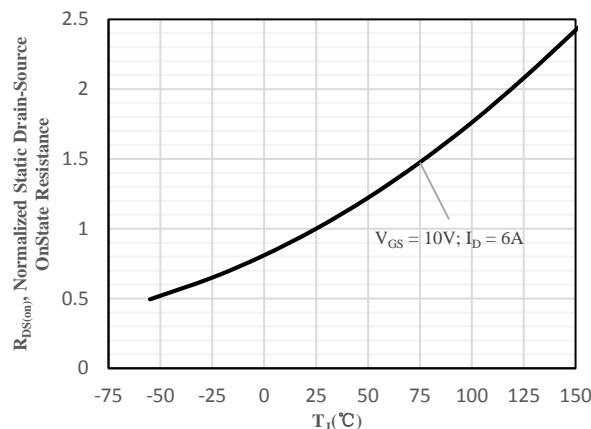


Fig 7 Normalized On-Resistance vs. Junction Temperature

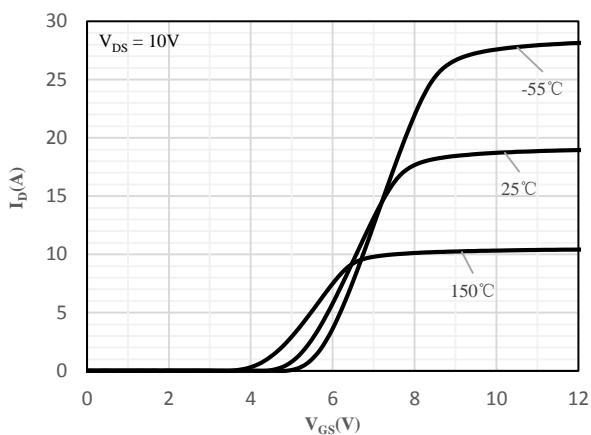


Fig 8 Transfer Characteristics

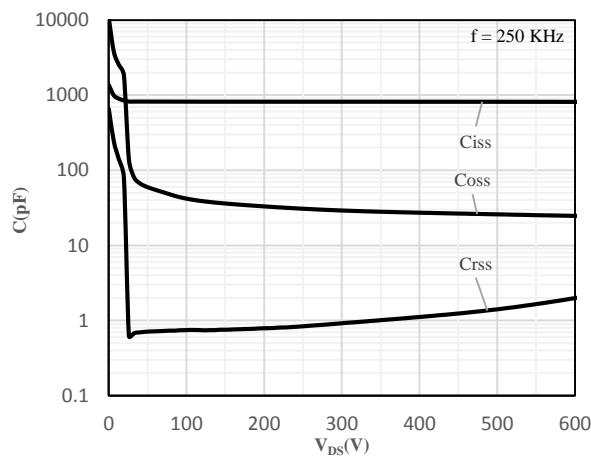


Fig 9 Capacitance Characteristics

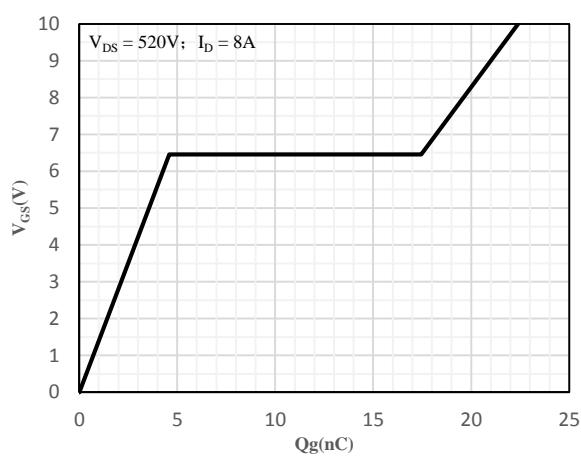


Fig 10 Gate-Charge Characteristics

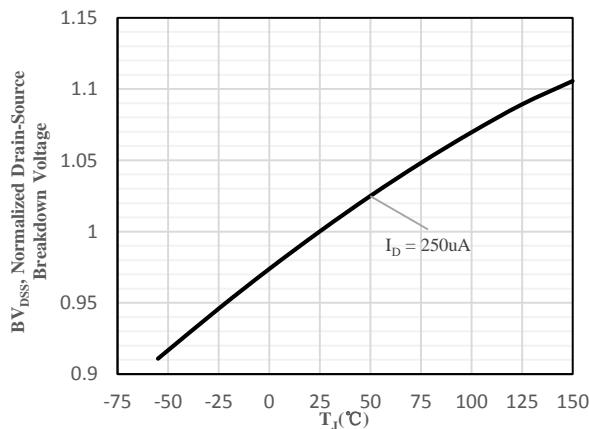


Fig 11 Normalized Breakdown Voltage vs. Junction Temperature

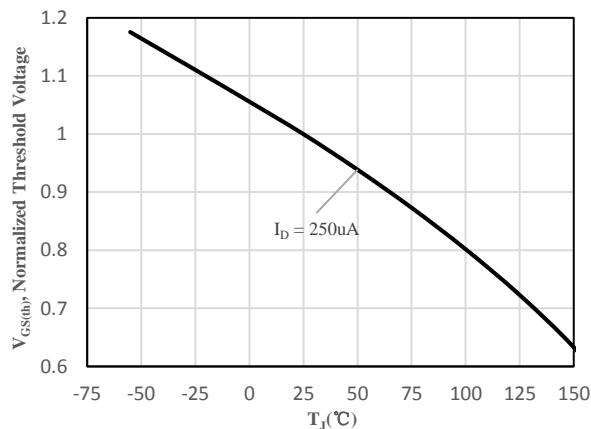


Fig 12 Normalized $V_{GS(th)}$ vs. Junction Temperature

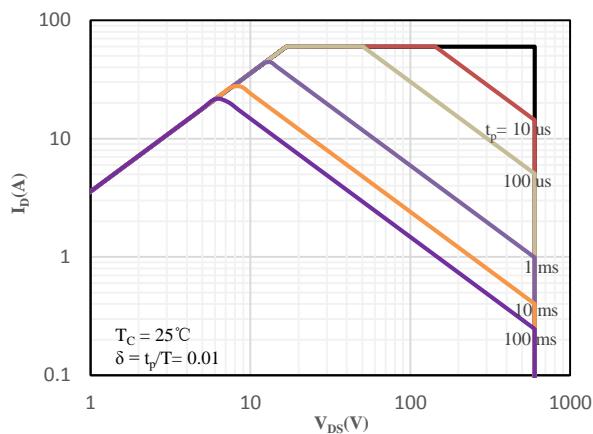


Fig 13 Safe Operating Area

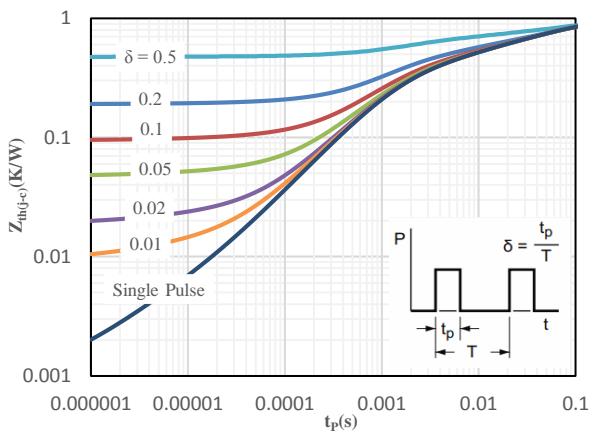
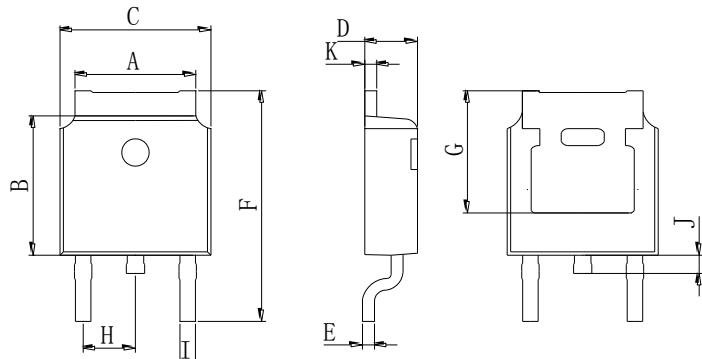


Fig 14 Maximum transient thermal impedance

Package Outline Dimensions (Unit: mm)



TO-252		
Dimension	Min.	Max.
A	5.05	5.65
B	5.80	6.40
C	6.25	6.85
D	2.20	2.40
E	0.40	0.60
F	9.71	10.31
G	5.05	5.65
H	2.10	2.50
I	0.70	0.90
J	0.50	0.70
K	0.40	0.60

Mounting Pad Layout (Unit: mm)

TO-252

